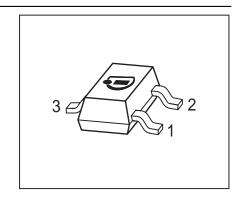


NPN Silicon RF Transistor

- Especially suitable for TV-Sat and UHF tuners
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101







ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BF775	LOs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	15	V	
Collector-emitter voltage	V _{CES}	20		
Collector-base voltage	V_{CBO}	20		
Emitter-base voltage	V_{EBO}	2.5		
Collector current	I _C	45	mA	
Base current	I _B	4		
Total power dissipation ²⁾	P _{tot}	280	mW	
<i>T</i> _S ≤ 48°C				
Junction temperature	T_{i}	150	°C	
Ambient temperature	T_{A}	-65 150		
Storage temperature	T_{stg}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ³⁾	R _{thJS}	≤ 365	K/W

¹Pb-containing package may be available upon special request

 $^{{}^2}T_{
m S}$ is measured on the collector lead at the soldering point to the pcb

 $^{^3}$ For calculation of R_{thJA} please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Symbol		Values	
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	15	-	-	V
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$					
Collector-emitter cutoff current	I _{CES}	-	-	10	μΑ
$V_{CE} = 20 \text{ V}, \ V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	100	μΑ
$V_{\rm EB} = 2.5 \text{ V}, I_{\rm C} = 0$					
DC current gain-	h _{FE}	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

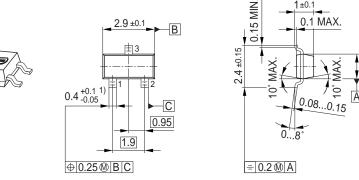
Parameter	Symbol		Values		Unit
		min.	typ.	max.	
AC Characteristics (verified by random samplin	g)				
Transition frequency	f_{T}	3.5	5	-	GHz
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.39	0.55	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0,$					
emitter grounded					
Collector emitter capacitance	C_{ce}	-	0.23	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0,$					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.64	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Noise figure	F				dB
$I_{\rm C} = 2 \text{ mA}, \ V_{\rm CE} = 6 \text{ V}, \ Z_{\rm S} = Z_{\rm Sopt},$					
f = 900 MHz		-	1.4	-	
f = 1.8 GHz		-	2	-	
Power gain, maximum available ¹⁾	G _{ma}				
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
$Z_{L} = Z_{Lopt}$, $f = 900 \text{ MHz}$		-	16	-	
f = 1.8 GHz		-	10.5	-	
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	13	-	
f = 1.8 GHz		_	7.5	_	

3

 $^{{}^{1}}G_{ma} = |S_{21}/S_{12}| (k-(k^{2}-1)^{1/2})$

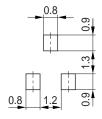


Package Outline

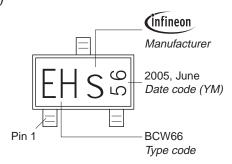


1) Lead width can be 0.6 max. in dambar area

Foot Print

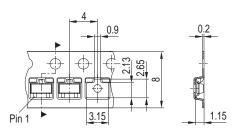


Marking Layout (Example)



Standard Packing

Reel Ø180 mm = 3.000 Pieces/Reel Reel Ø330 mm = 10.000 Pieces/Reel





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